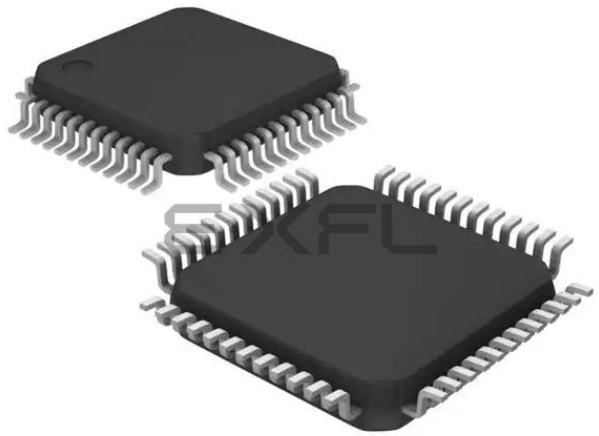


Welcome to E-XFL.COM

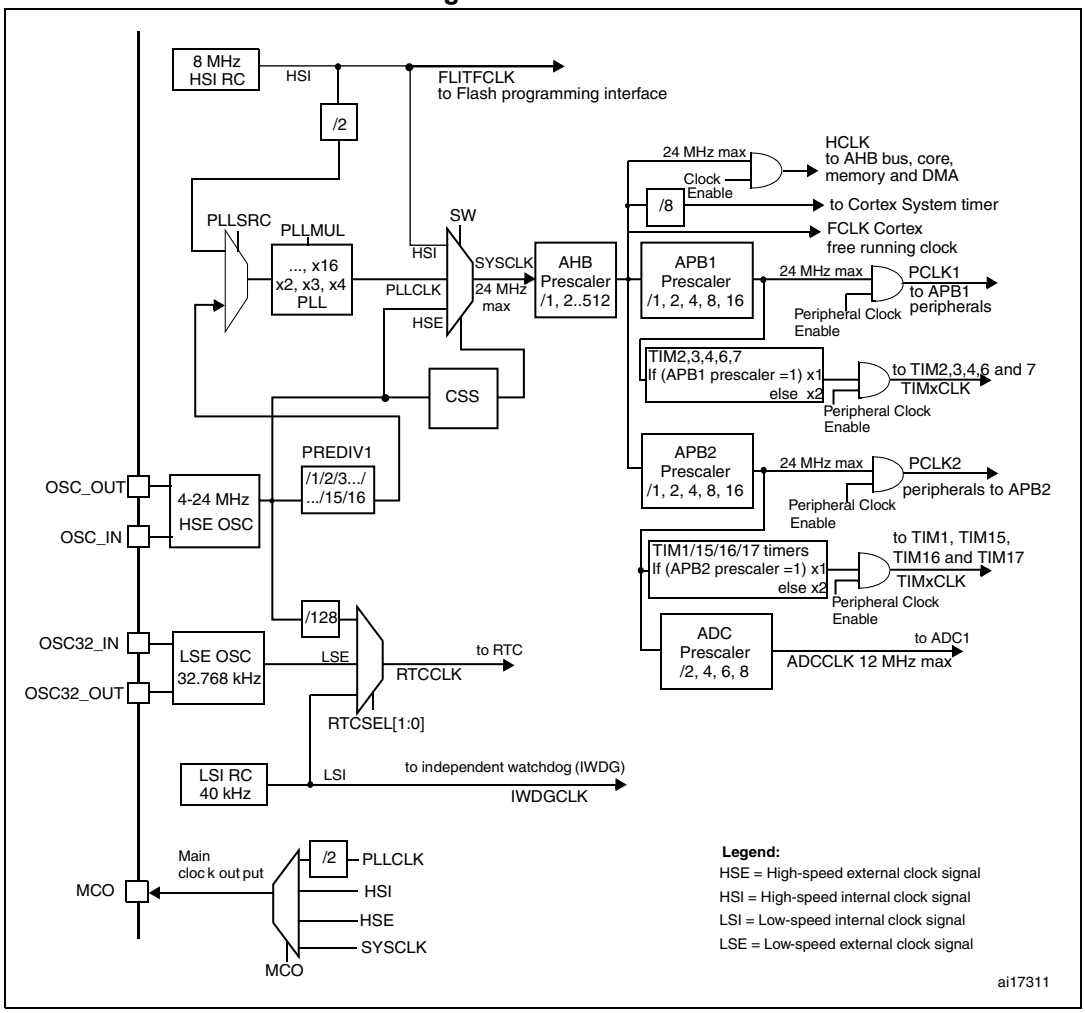
What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	37
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 10x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f100cbt6b

Figure 2. Clock tree



1. To have an ADC conversion time of 1.2 µs, APB2 must be at 24 MHz.

3 Pinouts and pin description

Figure 3. STM32F100xx value line LQFP100 pinout

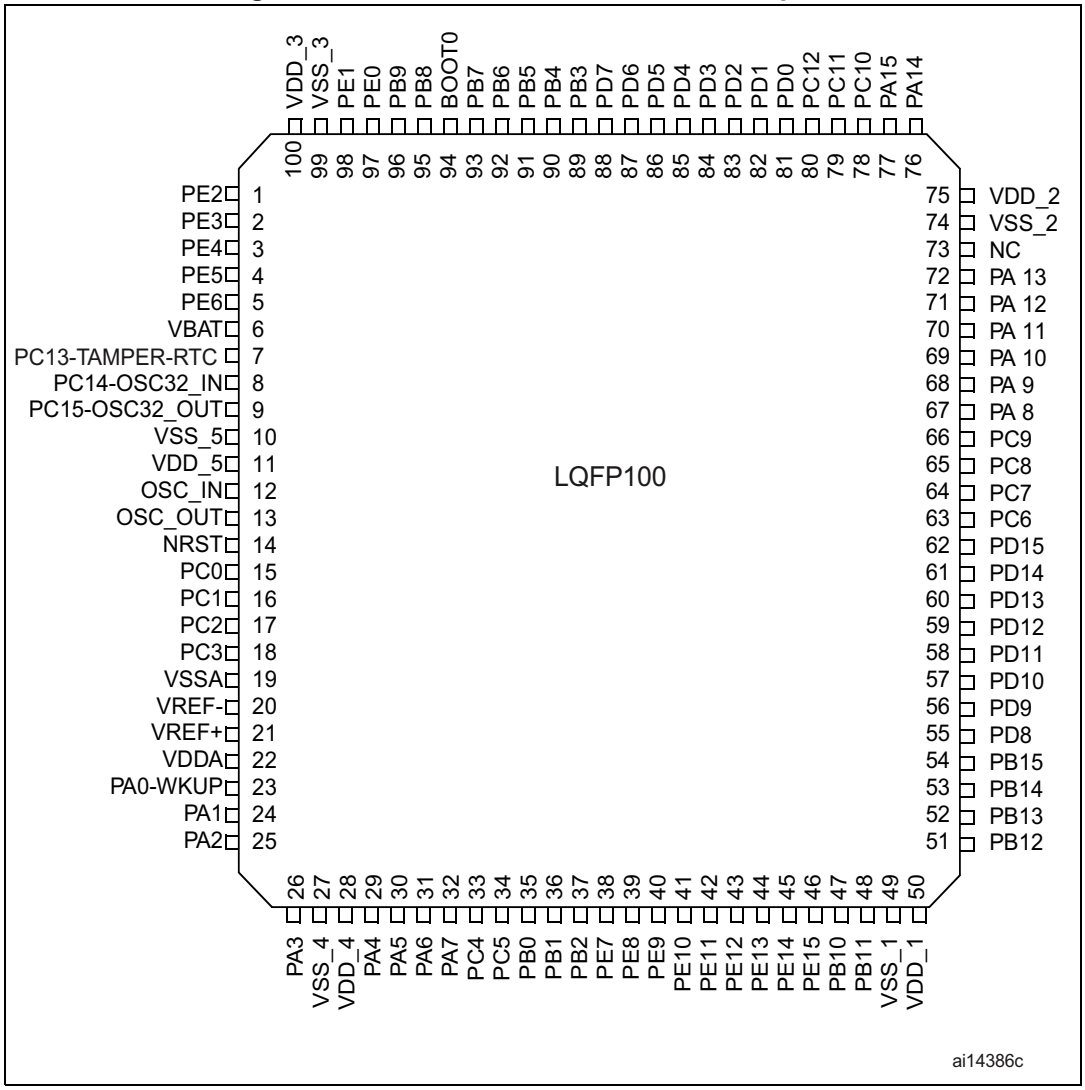


Figure 4. STM32F100xx value line LQFP64 pinout

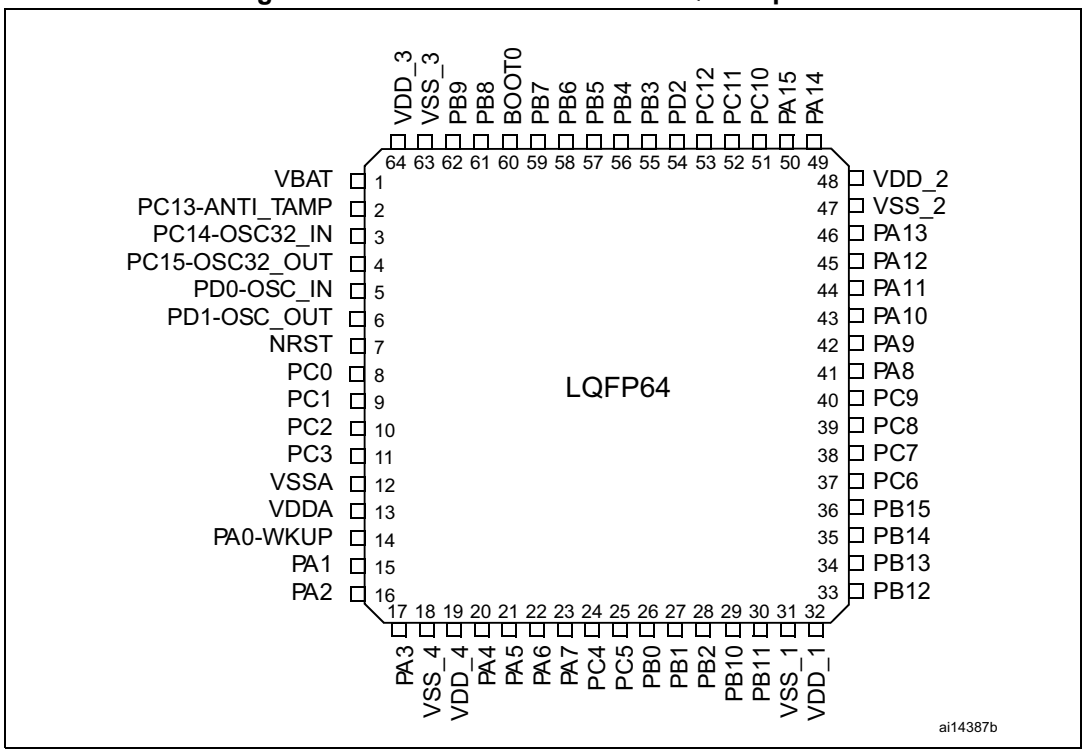


Figure 5. STM32F100xx value line LQFP48 pinout

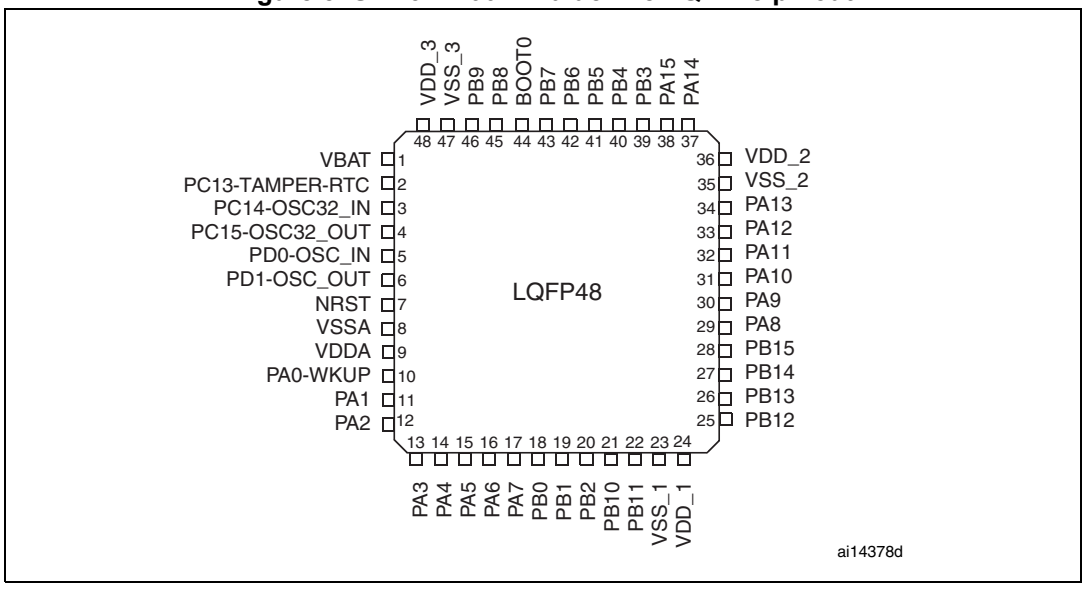


Figure 6. STM32F100xx value line TFBGA64 ballout

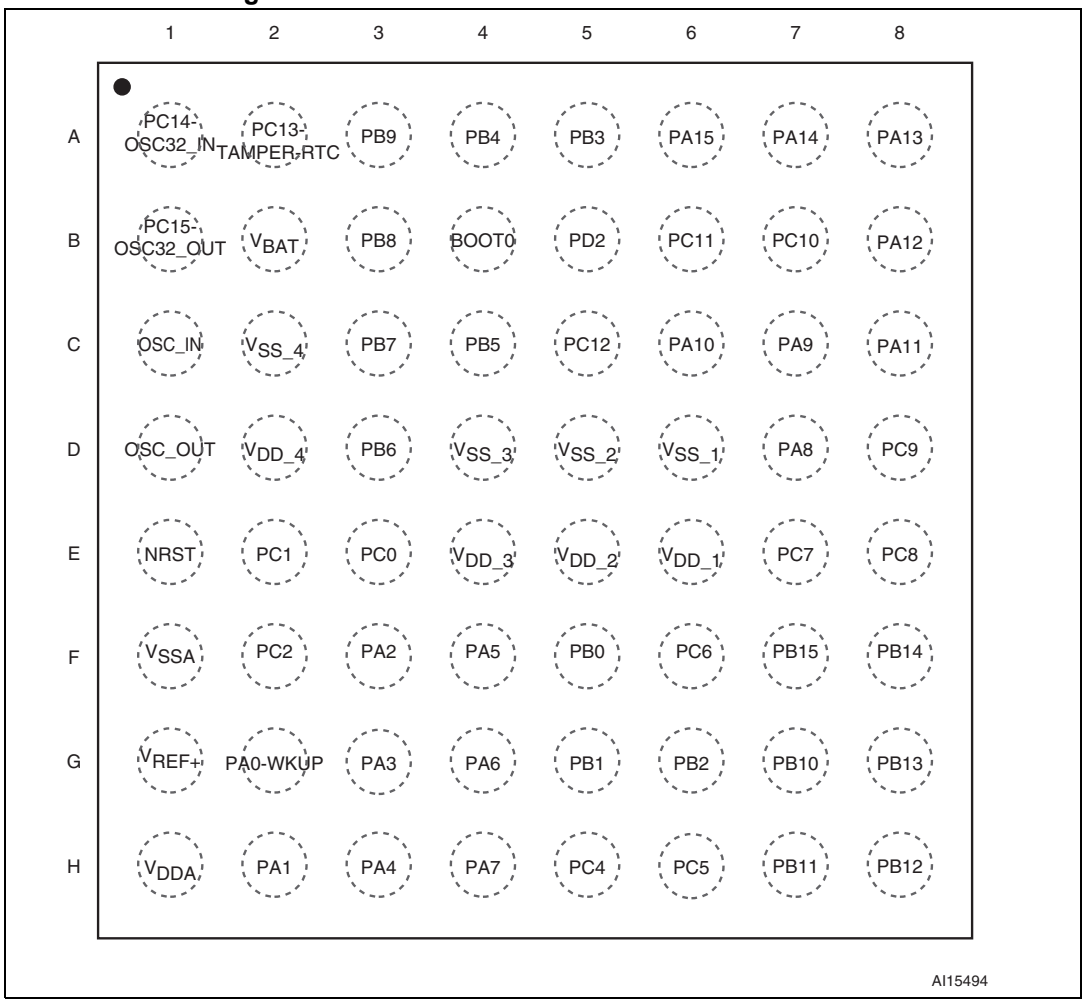


Table 4. Low & medium-density STM32F100xx pin definitions

Pins				Pin name	Type(1)	I / O level(2)	Main function(3) (after reset)	Alternate functions(3)(4)	
LQFP100	LQFP64	TFBGA64	LQFP48					Default	Remap
1	-	-	-	PE2	I/O	FT	PE2	TRACECLK	-
2	-	-	-	PE3	I/O	FT	PE3	TRACED0	-
3	-	-	-	PE4	I/O	FT	PE4	TRACED1	-
4	-	-	-	PE5	I/O	FT	PE5	TRACED2	-
5	-	-	-	PE6	I/O	FT	PE6	TRACED3	-
6	1	B2	1	V_{BAT}	S	-	V_{BAT}	-	-
7	2	A2	2	PC13-TAMPER-RTC(5)	I/O	-	PC13(6)	TAMPER-RTC	-
8	3	A1	3	PC14-OSC32_IN(5)	I/O	-	PC14(6)	OSC32_IN	-

Figure 8. Pin loading conditions

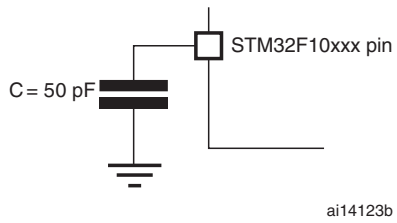
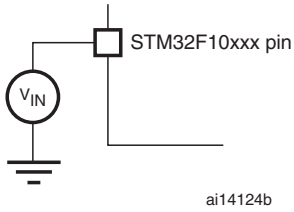
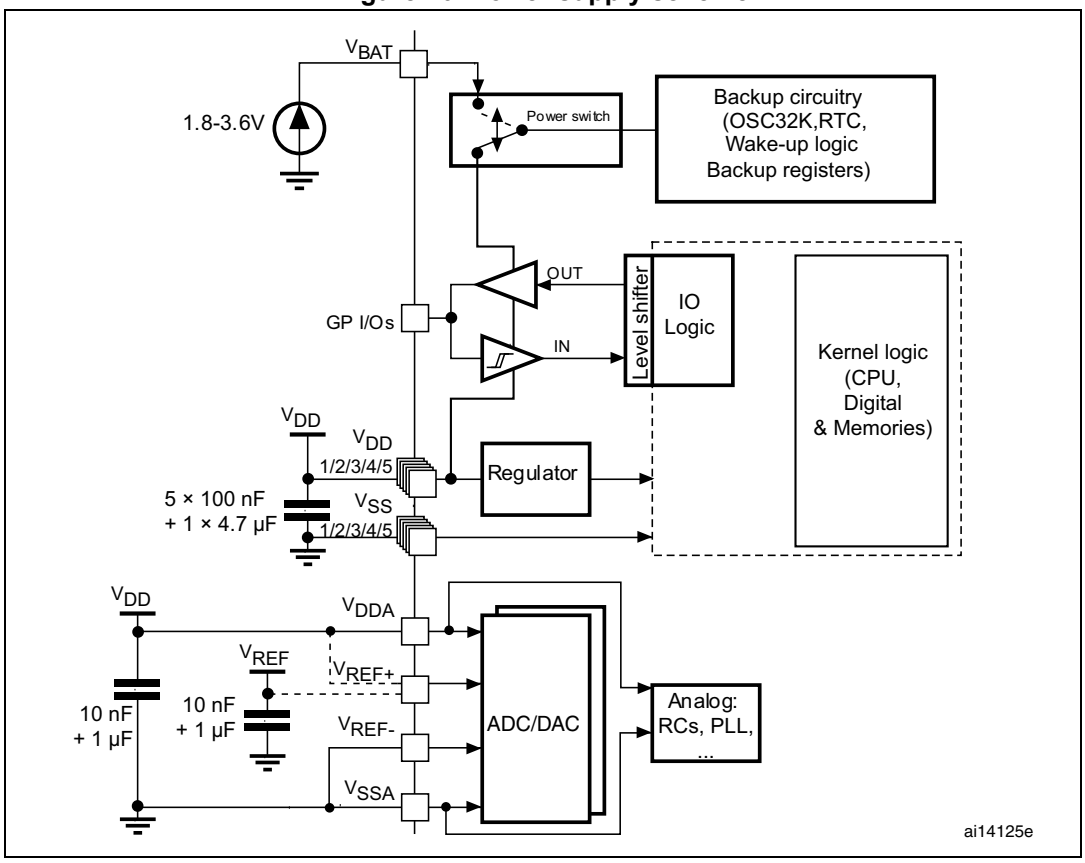


Figure 9. Pin input voltage



5.1.6 Power supply scheme

Figure 10. Power supply scheme



Caution: In *Figure 10*, the 4.7 µF capacitor must be connected to V_{DD3}.

Figure 15. Typical current consumption in Stop mode with regulator in Run mode versus temperature at V_{DD} = 3.3 V and 3.6 V

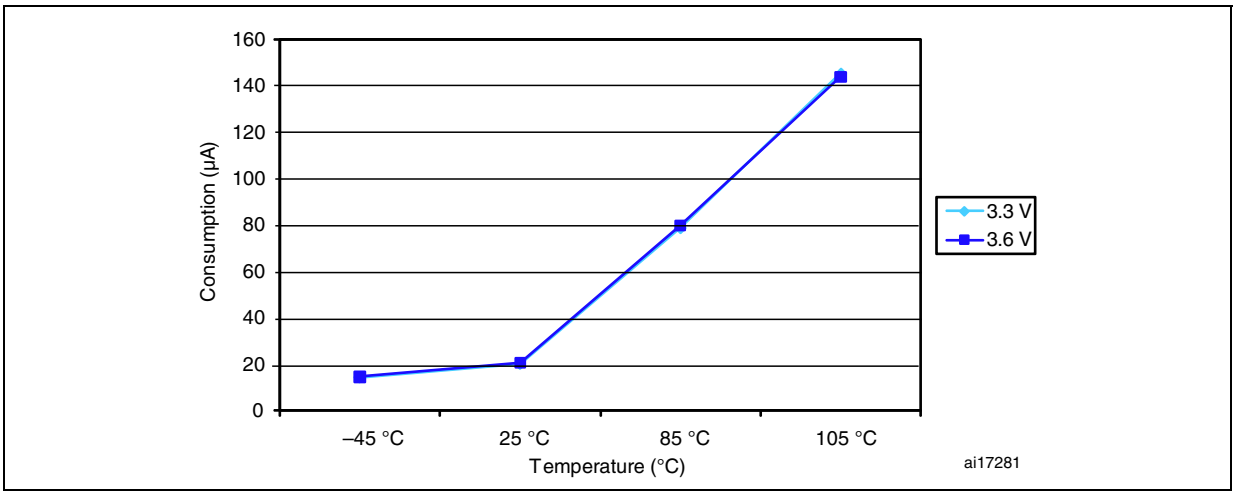
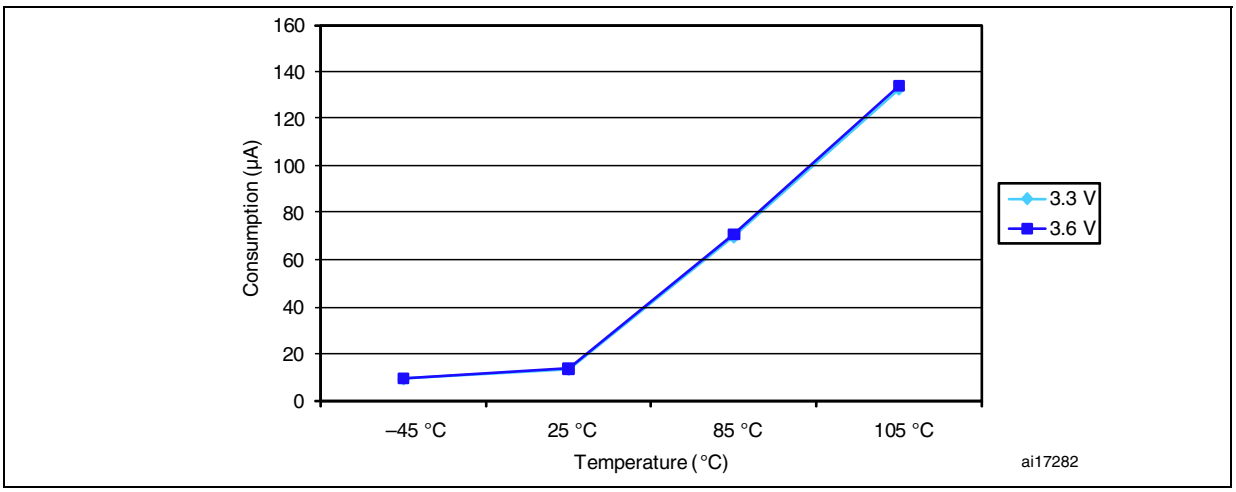


Figure 16. Typical current consumption in Stop mode with regulator in Low-power mode versus temperature at V_{DD} = 3.3 V and 3.6 V



Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 22*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Note: For C_{L1} and C_{L2} it is recommended to use high-quality ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator. C_{L1} and C_{L2}, are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}.
Load capacitance C_L has the following formula: $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{stray}$ where C_{stray} is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.
For further details, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Caution: To avoid exceeding the maximum value of C_{L1} and C_{L2} (15 pF) it is strongly recommended to use a resonator with a load capacitance $C_L \leq 7$ pF. Never use a resonator with a load capacitance of 12.5 pF.
Example: if you choose a resonator with a load capacitance of C_L = 6 pF, and C_{stray} = 2 pF, then $C_{L1} = C_{L2}$ = 8 pF.

Table 22. LSE oscillator characteristics (f_{LSE} = 32.768 kHz)(1)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R_F	Feedback resistor	-		-	5	-	MΩ
C_{L1} C_{L2}(2)	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S)(3)	R_S = 30 KΩ		-	-	15	pF
I_2	LSE driving current	V_{DD} = 3.3 V V_{IN} = V_{SS}		-	-	1.4	µA
g_m	Oscillator transconductance	-		5	-	-	µA/V
$t_{SU(LSE)}$(4)	Startup time	V_{DD} is stabilized	T_A = 50 °C	-	1.5	-	s
			T_A = 25 °C	-	2.5	-	
			T_A = 10 °C	-	4	-	
			T_A = 0 °C	-	6	-	
			T_A = -10 °C	-	10	-	
			T_A = -20 °C	-	17	-	
			T_A = -30 °C	-	32	-	
			T_A = -40 °C	-	60	-	

1. Guaranteed by characterization results.
2. Refer to the note and caution paragraphs above the table.
3. The oscillator selection can be optimized in terms of supply current using an high quality resonator with small R_S value for example MSIV-TIN32.768 kHz. Refer to crystal manufacturer for more details
4. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer

5.3.9 Memory characteristics

Flash memory

The characteristics are given at T_A = –40 to 105 °C unless otherwise specified.

Table 27. Flash memory characteristics

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
t_{prog}	16-bit programming time	T_A = –40 to +105 °C	40	52.5	70	µs
t_{ERASE}	Page (1 KB) erase time	T_A = –40 to +105 °C	20	-	40	ms
t_{ME}	Mass erase time	T_A = –40 to +105 °C	20	-	40	ms
I_{DD}	Supply current	Read mode f_{HCLK} = 24 MHz, V_{DD} = 3.3 V	-	-	20	mA
		Write / Erase modes f_{HCLK} = 24 MHz, V_{DD} = 3.3 V	-	-	5	mA
		Power-down mode / Halt, V_{DD} = 3.0 to 3.6 V	-	-	50	µA
V_{prog}	Programming voltage	-	2	-	3.6	V

1. Guaranteed by design.

Table 28. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value			Unit
			Min(1)	Typ	Max	
N_{END}	Endurance	T_A = –40 to +85 °C (6 suffix versions) T_A = –40 to +105 °C (7 suffix versions)	10	-	-	kcycles
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	-	-	Years
		1 kcycle(2) at T_A = 105 °C	10	-	-	
		10 kcycles(2) at T_A = 55 °C	20	-	-	

1. Based on characterization not tested in production.
2. Cycling performed over the whole temperature range.

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device is monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 30. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{HCLK}]	Unit
				8/24 MHz	
S_{EMI}	Peak level	V_{DD} = 3.6 V, T_A = 25°C, LQFP100 package compliant with SAE J1752/3	0.1 MHz to 30 MHz	9	dBµV
			30 MHz to 130 MHz	16	
			130 MHz to 1GHz	19	
			SAE EMI Level	4	-

5.3.11 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 31. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C conforming to JESD22-A114	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C conforming to JESD22-C101	III	500	

1. Based on characterization results, not tested in production.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD78 IC latch-up standard.

Table 32. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = +105 °C conforming to JESD78	II level A

Output voltage levels

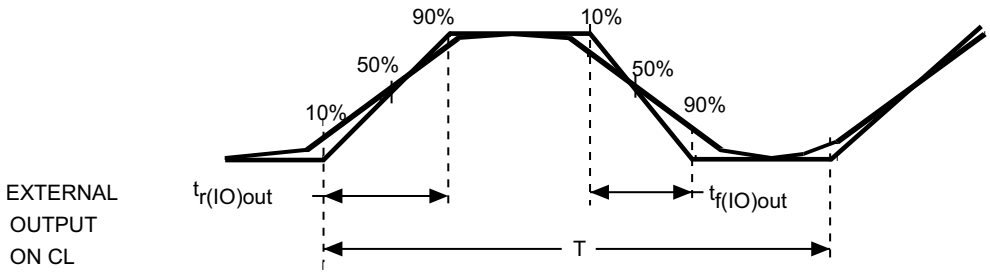
Unless otherwise specified, the parameters given in *Table 35* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 8*. All I/Os are CMOS and TTL compliant.

Table 35. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}(1)	Output Low level voltage for an I/O pin when 8 pins are sunk at the same time	CMOS port(2) I_{IO} = +8 mA, 2.7 V < V_{DD} < 3.6 V	-	0.4	V
V_{OH}(3)	Output High level voltage for an I/O pin when 8 pins are sourced at the same time		V_{DD}–0.4	-	
V_{OL}(1)	Output low level voltage for an I/O pin when 8 pins are sunk at the same time	TTL port(2) I_{IO} = +8 mA 2.7 V < V_{DD} < 3.6 V	-	0.4	V
V_{OH}(3)	Output high level voltage for an I/O pin when 8 pins are sourced at the same time		2.4	-	
V_{OL}(1)	Output low level voltage for an I/O pin when 8 pins are sunk at the same time	I_{IO} = +20 mA(4) 2.7 V < V_{DD} < 3.6 V	-	1.3	V
V_{OH} (3)	Output high level voltage for an I/O pin when 8 pins are sourced at the same time		V_{DD}–1.3	-	
V_{OL}(1)	Output low level voltage for an I/O pin when 8 pins are sunk at the same time	I_{IO} = +6 mA(4) 2 V < V_{DD} < 2.7 V	-	0.4	V
V_{OH}(3)	Output high level voltage for an I/O pin when 8 pins are sourced at the same time		V_{DD}–0.4	-	

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in *Table 6* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in *Table 6* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD}.
4. Based on characterization data, not tested in production.

Figure 26. I/O AC characteristics definition



Maximum frequency is achieved if (t_r + t_f) ≤ (2/3)T and if the duty cycle is (45-55%) when loaded by CL specified in the table " *I/O AC characteristics*".

ai14131d

5.3.14 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see *Table 34*).

Unless otherwise specified, the parameters given in *Table 37* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 8*.

Table 37. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}$(1)	NRST Input low level voltage	-	–0.5	-	0.8	V
$V_{IH(NRST)}$(1)	NRST Input high level voltage	-	2	-	V_{DD}+0.5	
$V_{hys(NRST)}$	NRST Schmitt trigger voltage hysteresis	-	-	200	-	mV
R_{PU}	Weak pull-up equivalent resistor(2)	$V_{IN} = V_{SS}$	30	40	50	kΩ
$V_{F(NRST)}$(1)	NRST Input filtered pulse	-	-	-	100	ns
$V_{NF(NRST)}$(1)	NRST Input not filtered pulse	-	300	-	-	ns

1. Guaranteed by design.
2. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).

5.3.16 Communications interfaces

I²C interface characteristics

Unless otherwise specified, the parameters given in *Table 39* are derived from tests performed under the ambient temperature, f_{PCLK1} frequency and V_{DD} supply voltage conditions summarized in *Table 8*.

The STM32F100xx value line I²C interface meets the requirements of the standard I²C communication protocol with the following restrictions: the I/O pins SDA and SCL are mapped to are not “true” open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.

The I²C characteristics are described in *Table 39*. Refer also to *Section 5.3.12: I/O current injection characteristics* for more details on the input/output alternate function characteristics (SDA and SCL).

Table 39. I²C characteristics

Symbol	Parameter	Standard mode I²C(1)		Fast mode I²C(1)(2)		Unit
		Min	Max	Min	Max	
$t_{w(SCLL)}$	SCL clock low time	4.7	-	1.3	-	µs
$t_{w(SCLH)}$	SCL clock high time	4.0	-	0.6	-	
$t_{su(SDA)}$	SDA setup time	250	-	100	-	ns
$t_{h(SDA)}$	SDA data hold time	0	-	0	900(3)	
$t_{r(SDA)}$ $t_{r(SCL)}$	SDA and SCL rise time	-	1000	-	300	
$t_{f(SDA)}$ $t_{f(SCL)}$	SDA and SCL fall time	-	300	-	300	
$t_{h(STA)}$	Start condition hold time	4.0	-	0.6	-	µs
$t_{su(STA)}$	Repeated Start condition setup time	4.7	-	0.6	-	
$t_{su(STO)}$	Stop condition setup time	4.0	-	0.6	-	µs
$t_{w(STO:STA)}$	Stop to Start condition time (bus free)	4.7	-	1.3	-	µs
C_b	Capacitive load for each bus line	-	400	-	400	pF

1. Guaranteed by design.
2. f_{PCLK1} must be at least 2 MHz to achieve standard mode I²C frequencies. It must be at least 4 MHz to achieve fast mode I²C frequencies. It must be a multiple of 10 MHz to reach the 400 kHz maximum I2C fast mode clock.
3. The maximum Data hold time has only to be met if the interface does not stretch the low period of SCL signal.

SPI interface characteristics

Unless otherwise specified, the parameters given in *Table 41* are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 8*.

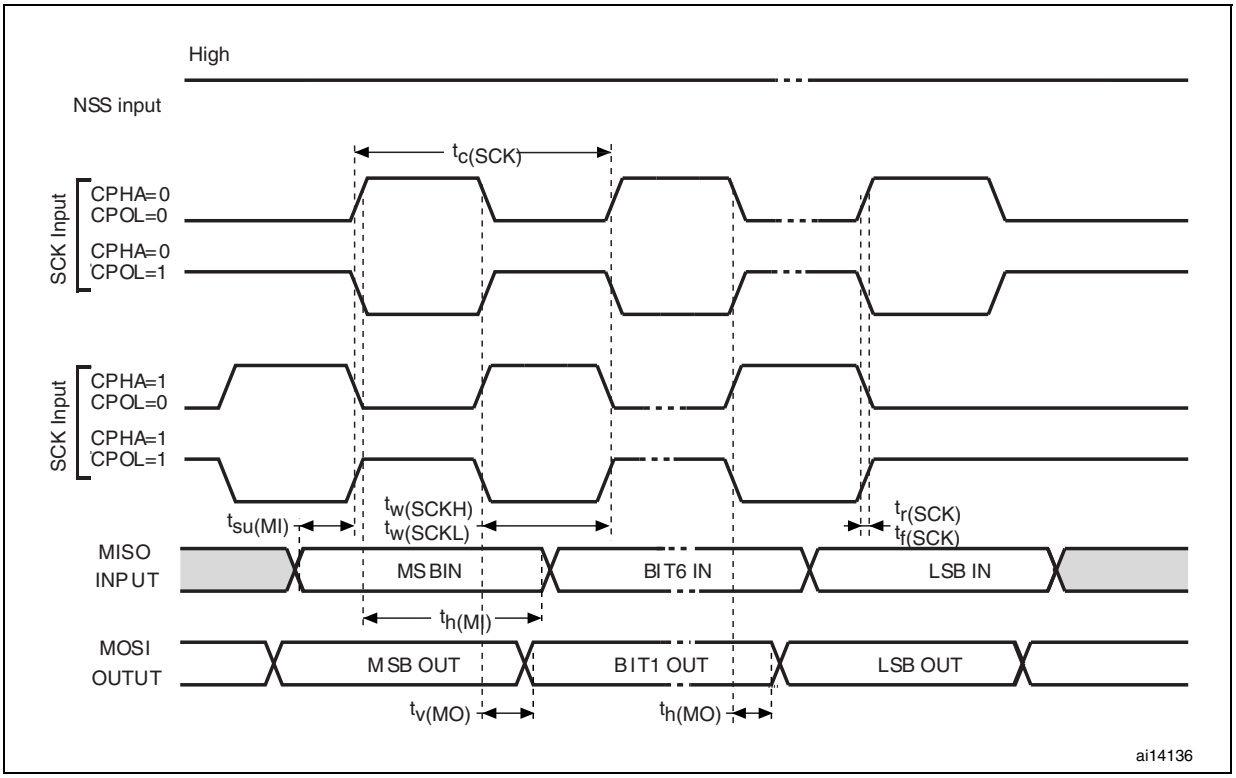
Refer to *Section 5.3.12: I/O current injection characteristics* for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 41. SPI characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	12	MHz
		Slave mode	-	12	
$t_{r(SCK)}$ $t_{f(SCK)}$	SPI clock rise and fall time	Capacitive load: C = 30 pF		8	ns
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	30	70	%
$t_{su(NSS)}$ (1)	NSS setup time	Slave mode	$4t_{PCLK}$	-	ns
$t_{h(NSS)}$ (1)	NSS hold time	Slave mode	$2t_{PCLK}$	-	
$t_{w(SCKH)}$ (1) $t_{w(SCKL)}$ (1)	SCK high and low time	Master mode, f_{PCLK} = 24 MHz, presc = 4	50	60	
$t_{su(MI)}$ (1) $t_{su(SI)}$ (1)	Data input setup time	Master mode	5	-	
		Slave mode	5	-	
$t_{h(MI)}$ (1)	Data input hold time	Master mode	5	-	
$t_{h(SI)}$ (1)		Slave mode	4	-	
$t_{a(SO)}$ (1)(2)	Data output access time	Slave mode, f_{PCLK} = 24 MHz	0	$3t_{PCLK}$	
$t_{dis(SO)}$ (1)(3)	Data output disable time	Slave mode	2	10	
$t_{v(SO)}$ (1)	Data output valid time	Slave mode (after enable edge)	-	25	
$t_{v(MO)}$ (1)	Data output valid time	Master mode (after enable edge)	-	5	
$t_{h(SO)}$ (1)	Data output hold time	Slave mode (after enable edge)	15	-	
$t_{h(MO)}$ (1)		Master mode (after enable edge)	2	-	

1. Guaranteed by characterization results.
2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z

Figure 31. SPI timing diagram - master mode(1)



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

HDMI consumer electronics control (CEC)

Refer to *Section 5.3.12: I/O current injection characteristics* for more details on the input/output alternate function characteristics.

5.3.17 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 42* are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DDA} supply voltage conditions summarized in *Table 8*.

Note: It is recommended to perform a calibration after each power-up.

Table 42. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Power supply	-	2.4	-	3.6	V
V_{REF+}	Positive reference voltage	-	2.4	-	V_{DDA}	V
I_{VREF}	Current on the V_{REF} input pin	-	-	160(1)	220(1)	µA
f_{ADC}	ADC clock frequency	-	0.6	-	12	MHz
f_S(2)	Sampling rate	-	0.05	-	1	MHz
f_{TRIG}(2)	External trigger frequency	f_{ADC} = 12 MHz	-	-	705	kHz
		-	-	-	17	$1/f_{ADC}$
V_{AIN}(3)	Conversion voltage range	-	0 (V_{SSA} tied to ground)	-	V_{REF+}	V
R_{AIN}(2)	External input impedance	See *Equation 1* and *Table 43* for details	-	-	50	kΩ
R_{ADC}(2)	Sampling switch resistance	-	-	-	1	kΩ
C_{ADC}(2)	Internal sample and hold capacitor	-	-	-	8	pF
t_{CAL}(2)	Calibration time	f_{ADC} = 12 MHz	6.9			µs
		-	83			$1/f_{ADC}$
t_{lat}(2)	Injection trigger conversion latency	f_{ADC} = 12 MHz	-	-	0.25	µs
		-	-	-	3(4)	$1/f_{ADC}$
t_{latr}(2)	Regular trigger conversion latency	f_{ADC} = 12 MHz	-	-	0.166	µs
		-	-	-	2(4)	$1/f_{ADC}$
t_S(2)	Sampling time	f_{ADC} = 12 MHz	0.125	-	20.0	µs
			1.5	-	239.5	$1/f_{ADC}$
t_{STAB}(2)	Power-up time	-	0	0	1	µs
t_{CONV}(2)	Total conversion time (including sampling time)	f_{ADC} = 12 MHz	1.17	-	21	µs
		-	14 to 252 (t_S for sampling +12.5 for successive approximation)			$1/f_{ADC}$

1. Based on characterization results, not tested in production.
2. Guaranteed by design.
3. V_{REF+} can be internally connected to V_{DDA} and V_{REF-} can be internally connected to V_{SSA}, depending on the package. Refer to *Table 4: Low & medium-density STM32F100xx pin definitions* and *Figure 6* for further details.
4. For external triggers, a delay of $1/f_{PCLK2}$ must be added to the latency specified in *Table 42*.

Equation 1: R_{AIN} max formula:

$$R_{AIN} < \frac{T_S}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

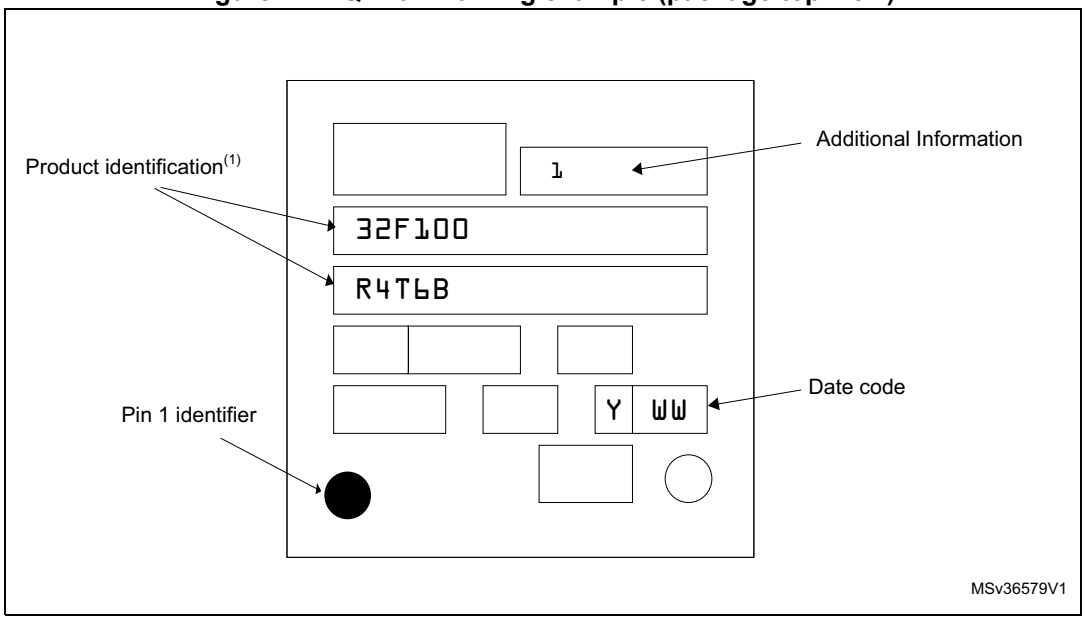
The above formula (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Device marking for LQFP64

The following figure gives an example of topside marking and pin 1 position identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 42. LQFP64 marking example (package top view)



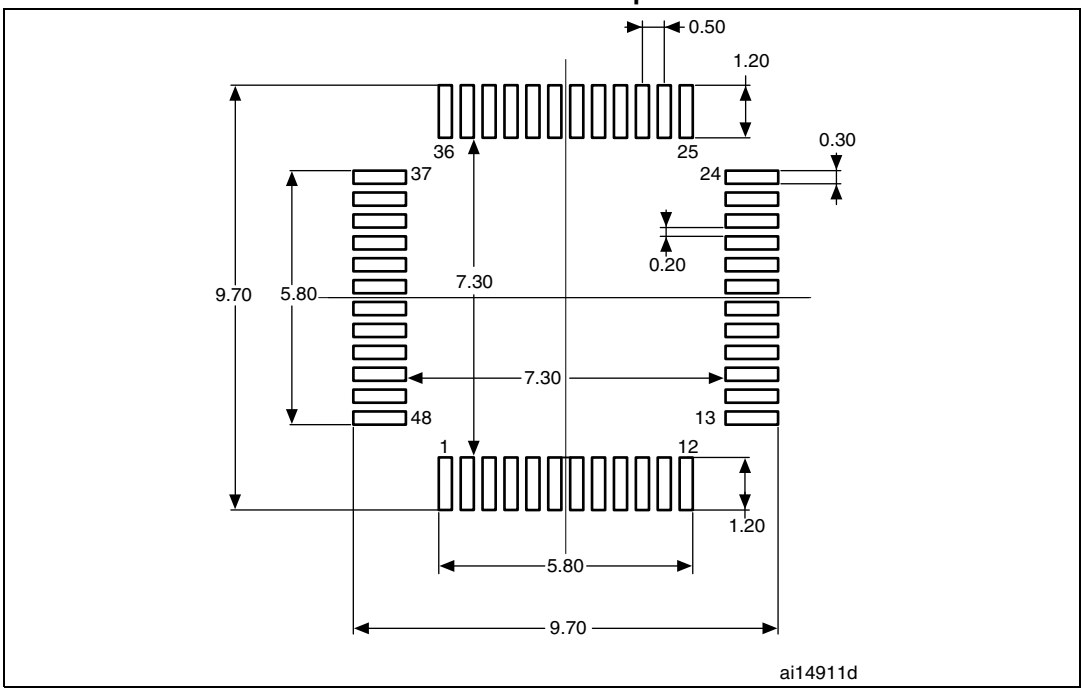
1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Table 52. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835
E3	-	5.500	-	-	0.2165	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 47. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package recommended footprint



1. Dimensions are expressed in millimeters.

6.5.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the ordering information scheme shown in *Table 54: Ordering information scheme*.

Each temperature range suffix corresponds to a specific guaranteed ambient temperature at maximum dissipation and, to a specific maximum junction temperature.

As applications do not commonly use the STM32F10xxx at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine which temperature range will be best suited to the application.

The following examples show how to calculate the temperature range needed for a given application.

Example: high-performance application

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 82 °C (measured according to JESD51-2), I_{DDmax} = 50 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V and maximum 8 I/Os used at the same time in output mode at low level with I_{OL} = 20 mA, V_{OL}= 1.3 V

P_{INTmax} = 50 mA × 3.5 V= 175 mW

P_{IOmax} = 20 × 8 mA × 0.4 V + 8 × 20 mA × 1.3 V = 272 mW

This gives: P_{INTmax} = 175 mW and P_{IOmax} = 272 mW

P_{Dmax} = 175 + 272 = 447 mW

Thus: P_{Dmax} = 447 mW

Using the values obtained in *Table 53* T_{Jmax} is calculated as follows:

– For LQFP64, 45 °C/W

T_{Jmax} = 82 °C + (45 °C/W × 447 mW) = 82 °C + 20.1 °C = 102.1 °C

This is within the range of the suffix 6 version parts (–40 < T_J < 105 °C).

In this case, parts must be ordered at least with the temperature range suffix 6 (see *Table 54: Ordering information scheme*).

Example 2: High-temperature application

Using the same rules, it is possible to address applications that run at high ambient temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 115 °C (measured according to JESD51-2), I_{DDmax} = 20 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V

P_{INTmax} = 20 mA × 3.5 V= 70 mW

P_{IOmax} = 20 × 8 mA × 0.4 V = 64 mW

This gives: P_{INTmax} = 70 mW and P_{IOmax} = 64 mW:

P_{Dmax} = 70 + 64 = 134 mW

Thus: P_{Dmax} = 134 mW

7 Ordering information scheme

Table 54. Ordering information scheme

Example: STM32 F 100 C 6 T 6 B xxx

Device family

STM32 = ARM-based 32-bit microcontroller

Product type

F = General-purpose

Device subfamily

100 = value line

Pin count

C = 48 pins

R = 64 pins

V = 100 pins

Flash memory size

4 = 16 Kbytes of Flash memory

6 = 32 Kbytes of Flash memory

8 = 64 Kbytes of Flash memory

B = 128 Kbytes of Flash memory

Package

T = LQFP

H = BGA

Temperature range

6 = Industrial temperature range, –40 to 85 °C

7 = Industrial temperature range, –40 to 105 °C

Internal code

B

Options

xxx = programmed parts

TR = tape and real

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

Table 55. Document revision history (continued)

Date	Revision	Changes
30-Mar-2010	3	Revision history corrected. Updated *Table 6: Current characteristics* Values and note updated in *Table 16: Typical current consumption in Run mode, code with data processing running from Flash* and *Table 17: Typical current consumption in Sleep mode, code running from Flash or RAM*. Updated *Table 15: Typical and maximum current consumptions in Stop and Standby modes* Added *Figure 14: Typical current consumption on VBAT with RTC on vs. temperature at different VBAT values* Typical consumption for ADC1 corrected in *Table 18: Peripheral current consumption*. *Maximum current consumption* and *Typical current consumption*: frequency conditions corrected. *Output driving current* corrected. Updated *Table 30: EMI characteristics* f_{ADC} max corrected in *Table 42: ADC characteristics*. Small text changes.
06-May-2010	4	Updated *Table 31: ESD absolute maximum ratings on page 55* and *Table 32: Electrical sensitivities on page 56* Updated *Table 44: ADC accuracy - limited test conditions on page 70* and *Table 45: ADC accuracy on page 70*
12-Jul-2010	5	Updated *Table 24: LSI oscillator characteristics on page 51* Updated *Table 44: ADC accuracy - limited test conditions on page 70* and *Table 45: ADC accuracy on page 70*
04-Apr-2011	6	Updated *Figure 2: Clock tree* to add FLITF clock Updated footnotes below *Table 5: Voltage characteristics on page 33* and *Table 6: Current characteristics on page 34* Updated tw min in *Table 19: High-speed external user clock characteristics on page 46* Updated startup time in *Table 22: LSE oscillator characteristics (fLSE = 32.768 kHz) on page 49* Updated *Table 23: HSI oscillator characteristics on page 50* Added *Section 5.3.12: I/O current injection characteristics on page 56* Updated *Table 34: I/O static characteristics on page 57* Corrected TTL and CMOS designations in *Table 35: Output voltage characteristics on page 60* Removed note on remapped characteristics from *Table 41: SPI characteristics on page 66*